Switch-mode NPN Silicon Power Transistors

The BUX85G is designed for high voltage, high speed power switching applications like converters, inverters, switching regulators, motor control systems.

Features

• These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO(sus)}	450	Vdc
Collector–Emitter Voltage	V _{CES}	1000	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current – Continuous	I _C	2	Adc
Collector Current - Peak (Note 1)	I _{CM}	3.0	Adc
Base Current – Continuous	I _B	0.75	Adc
Base Current – Peak (Note 1)	I _{BM}	1.0	Adc
Reverse Base Current – Peak	I _{BM}	1	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	50 0.4	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

THERMAL CHARACTERISTICS

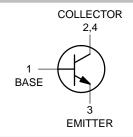
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	TL	275	°C

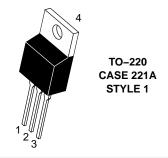


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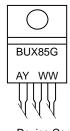
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2.0 AMPERES POWER TRANSISTOR NPN SILICON 450 VOLTS, 50 WATTS





MARKING DIAGRAM



BUX85 = Device Code A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BUX85G	TO-220 (Pb-Free)	50 Units / Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERIST	FICS (Note 2)			1 -34	1 111	1
Collector–Emitter Sus (I _C = 100 mAdc, (L	V _{CEO(sus)}	450	-	-	Vdc	
Collector Cutoff Curre (V _{CES} = Rated Valu (V _{CES} = Rated Valu	I _{CES}	_ _		0.2 1.5	mAdc	
Emitter Cutoff Curren (V _{EB} = 5 Vdc, I _C =	I _{EBO}	-	_	1	mAdc	
ON CHARACTERISTI	ICS (Note 2)	<u>.</u>				
DC Current Gain (I _C = 0.1 Adc, V _{CE} = 5 V)		h _{FE}	30	50	_	_
Collector–Emitter Saturation Voltage ($I_C = 0.3$ Adc, $I_B = 30$ mAdc) ($I_C = 1$ Adc, $I_B = 200$ mAdc)		V _{CE(sat)}	_ _	-	0.8 1	Vdc
Base–Emitter Saturat (I _C = 1 Adc, I _B = 0.2	V _{BE(sat)}	-	-	1.1	Vdc	
DYNAMIC CHARACT	ERISTICS			•		•
Current–Gain – Band (I _C = 500 mAdc, V _C	f _T	4	_	_	MHz	
SWITCHING CHARAC	CTERISTICS	•	•	•		
Turn-on Time	V _{CC} = 250 Vdc, I _C = 1 A	t _{on}	_	0.3	0.5	μS
Storage Time	$I_{B1} = 0.2 \text{ A}, I_{B2} = 0.4 \text{ A}$	t _s	_	2	3.5	μS
Fall Time	See Figure 2	t _f	_	0.3	_	μS
Fall Time	Same above cond. at T _C = 95°C	t _f	-	-	1.4	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: PW = 300 μs, Duty Cycle ≤2%.

TYPICAL CHARACTERISTICS

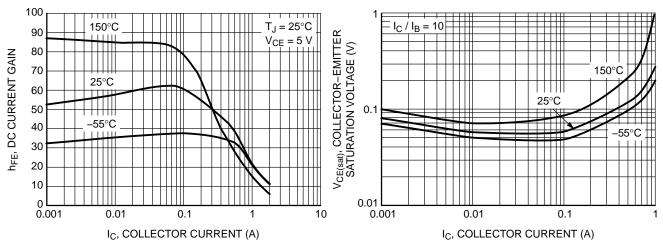


Figure 1. DC Current Gain

Figure 2. V_{CE(sat)}, Collector Emitter Saturation Voltage

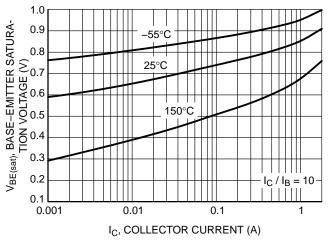


Figure 3. V_{BE(sat)}, Base Emitter Saturation Voltage

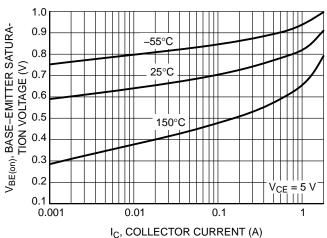


Figure 4. $V_{BE(on)}$, Base Emitter On Voltage

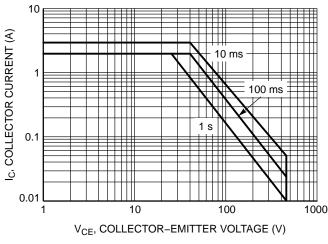


Figure 5. Safe Operating Area (SOA)

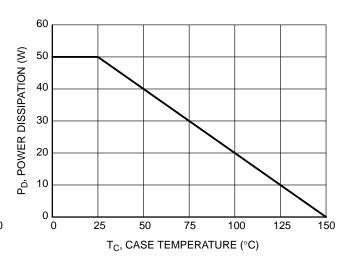


Figure 6. Power Derating

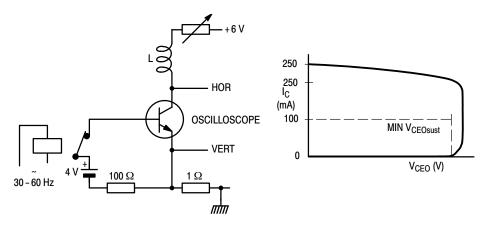
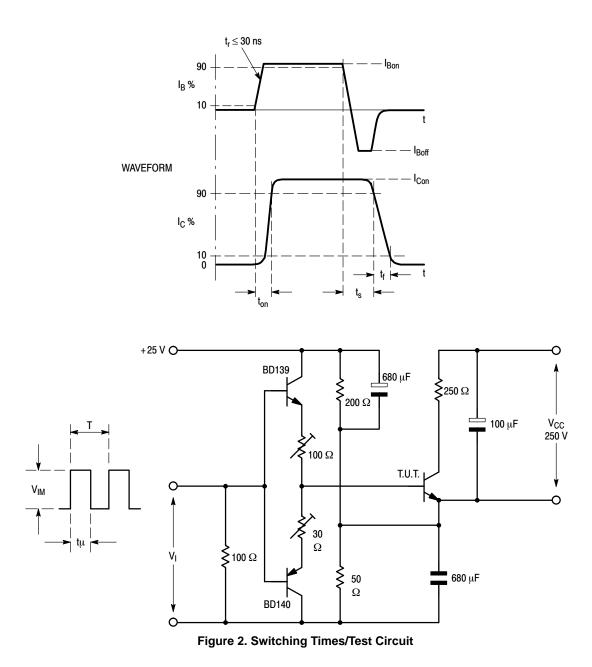


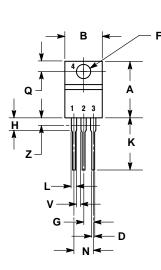
Figure 1. Test Circuit for V_{CEOsust}

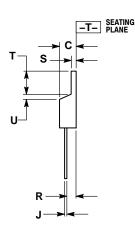


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PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

MULIMETERS

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

BASE PIN 1.

COLLECTOR

EMITTER 3

COLLECTOR

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